

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/786,511	02/25/2004	Richard P. Schubert	A0312.70522US00	5018
7:	590 11/29/2005		EXAMINER	
Jamie H. Rose			LAM, DAVID	
Wolf, Greenfie	ld & Sacks, P.C.			
600 Atlantic Av	venue		ART UNIT	PAPER NUMBER
Boston, MA	02210		2827	

DATE MAILED: 11/29/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

		•	
	Application No.	Applicant(s)	
	10/786,511	SCHUBERT, RICHARD P.	
Office Action Summary	Examiner	Art Unit	
	David Lam	2827	
The MAILING DATE of this communication a Period for Reply	ppears on the cover sheet wit	h the correspondence address	
A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a re - If NO period for reply is specified above, the maximum statutory perions - Failure to reply within the set or extended period for reply will, by stat Any reply received by the Office later than three months after the main earned patent term adjustment. See 37 CFR 1.704(b).	I. 1.136(a). In no event, however, may a re eply within the statutory minimum of thirty of will apply and will expire SIX (6) MONT ute, cause the application to become AB/	ply be timely filed (30) days will be considered timely. "HS from the mailing date of this communication. ANDONED (35 U.S.C. § 133).	
Status		·	
1) Responsive to communication(s) filed on		•	
• — •	nis action is non-final.		
3) Since this application is in condition for allow		ers, prosecution as to the merits is	
closed in accordance with the practice unde			
Disposition of Claims			
4) Claim(s) 1-22 is/are pending in the application			
4a) Of the above claim(s) is/are withdo	rawn from consideration.		
5)⊠ Claim(s) <u>16-22</u> is/are allowed.			
6)⊠ Claim(s) <u>1,4 and 8-12,15</u> is/are rejected.			
7) Claim(s) <u>2,3,5-7,13 and 14</u> is/are objected to		·	
8) Claim(s) are subject to restriction and	l/or election requirement.		
Application Papers	·		
9) The specification is objected to by the Exami			
10)⊠ The drawing(s) filed on <u>08 November 2004</u> is	s/are: a)□ accepted or b)⊠	objected to by the Examiner.	
Applicant may not request that any objection to the	ne drawing(s) be held in abeyand	ce. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the corre	ection is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
11)☐ The oath or declaration is objected to by the	Examiner. Note the attached	Office Action or form PTO-152.	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a life.	ents have been received. ents have been received in Apriority documents have been eau (PCT Rule 17.2(a)).	oplication No received in this National Stage	
Attachment(s)	_		
1) Notice of References Cited (PTO-892)		ummary (PTO-413))/Mail Date	
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 	T	formal Patent Application (PTO-152)	
Paper No(s)/Mail Date <u>2/25/04</u> .	6) Other:	<u>-</u> ·	

DETAILED ACTION

Drawings

1. The drawing are objected to because On Figure 1, output node "135" should be changed to -- 125 --. Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. The figure or figure number of an amended drawing should not be labeled as "amended." If a drawing figure is to be canceled, the appropriate figure must be removed from the replacement sheet, and where necessary, the remaining figures must be renumbered and appropriate changes made to the brief description of the several views of the drawings for consistency. Additional replacement sheets may be necessary to show the renumbering of the remaining figures. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Specification

2. The disclosure is objected to because of the following informalities: On page 7, line 14, "memory cell 135" should be change to -- memory cell 110 --. Appropriate correction is required.

Application/Control Number: 10/786,511 Page 3

Art Unit: 2827

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 1, 4, 8-10 are rejected under 35 U.S.C. 102(b) as being anticipated by Nagatomo (6,243,297).

Regarding to claims 1, 4, 8-10, Nagatomo discloses a memory device comprising: a write circuit (40) defining an output node, and selectable connecting at least one memory cell to the output node to permit a discharge associated with a write operation to flow to the output node; a write strength selection circuit (30, 50) that modifies at least one characteristic of the discharge flowing to the output node; wherein the at least one characteristic is at least one of a current level and a quantity of charge; wherein the at least one memory cell comprises a plurality of memory cells arranged in a plurality of rows and a plurality of columns, and further comprising a plurality of pass circuit (transistors connected to Y₀, Y₁); wherein the write circuit comprises at least one inverter; wherein the discharge flowing to the output node flows through the output node. See Figs. 1, 4-7; Cols. 5-6; 9-11.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are

such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 11, 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nagatomo (6,243,297).

With respect to claims 11, 15 although Nagatomo discloses all the elements of the memory device as applied to claim 1 above but lack an inclusion of wherein the at least one memory cell comprises a plurality of static random access memory (SRAM) cells; and at least one failure-analysis memory cell that has an intentional defect. The use of a static random access memory (SRAM) cells and the at least one failure-analysis memory cell within a semiconductor memory device would have been known and available in the art. It would have been obvious to one having ordinary skill in the art at the time of the invention to modify accordingly in order to improve efficiency of faulty analysis in a semiconductor memory device. *Note: Col. 5, lines 47-65 of Hamada (6,363,500) cited to support known position.*

5. Claim 12 rejected under 35 U.S.C. 103(a) as being unpatentable over Nagatomo (6,243,297) in view of Tsuda et al. (6,808,124).

Nagatomo disclose a memory device comprising a write circuit (40) that selectably connected to at least one memory cell to an output node via one of a bit line and a complementary bit lines (See Fig. 1).

Nagatomo fails to disclose wherein the write circuit comprises three inverters.

Tsuda et al. Disclose a memory device comprising a write circuit (1) comprise three inverters. (See Fig. 1)

Application/Control Number: 10/786,511 Page 5

Art Unit: 2827

It would have been obvious to one having ordinary skill in the art at the time of the invention to provide the write circuit of Nagatomo that comprises three inverter as taught by Tsuda et al. to provide a high-speed, size and cost reduction semiconductor memory device.

Allowable Subject Matter

6. Claims 2-3, 6-7, 13-14 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record fails to teach the above noted memory device and wherein the write strength selector circuit has a strong write state associated with a first value of the at least one characteristic, and a weak write state associated with a second value of the at least one characteristic.

7. The following is an examiner's statement of reasons for allowance: Claims 16-22 are allowable over the prior art of record because none of the prior art whether taken singularly or in combination, especially when these limitations are considered within the specific combination claimed, to teach: method for testing a memory device comprising step of directing a weak write operation to at least one memory cell by controlling at least one characteristic of the discharge flowing to the output node, and among other steps as claimed in independent claims 16, 21.

Conclusion

Application/Control Number: 10/786,511

Art Unit: 2827

The prior art made of record and not relied upon is considered pertinent to applicant's 8.

disclosure.

- Adam et al. (6,657,886) disclose a split local and continuous bit line for fast domino

read SRAM.

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to David Lam whose telephone number is 571-272-1782. The

examiner can normally be reached on 6:00 - 4:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Zarabian Amir can be reached on 571-272-1852852. The fax phone numbers for the

organization where this application or proceeding is assigned is (571) 272-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

D. Lam

November 25, 2005

Page 6